

# **FDS3580**

## 80V N-Channel PowerTrench™ MOSFET

### **General Description**

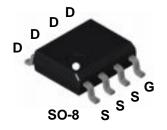
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

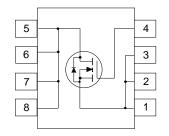
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\scriptscriptstyle DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### **Features**

- 7.6 A, 80 V.  $R_{DS(ON)} = 0.027 \Omega @ V_{GS} = 10 V$   $R_{DS(ON)} = 0.031 \Omega @ V_{GS} = 6 V.$
- Low gate charge (34nC typical).
- Fast switching speed.
- $\bullet$  High performance trench technology for extremely low  $R_{\mbox{\tiny DS(ON)}}.$
- High power and current handling capability.





Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{DSS}$	Drain-Source Voltage		80	V
$V_{GSS}$	Gate-Source Voltage		<u>±</u> 20	V
$I_D$	Drain Current - Continuous	(Note 1a)	7.6	Α
	- Pulsed		50	
$P_D$	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1	
$T_J$ , $T_{stg}$	Operating and Storage Junction Temperatu	-55 to +150	∘C	

### **Thermal Characteristics**

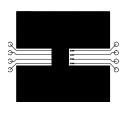
$R_{ heta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta^{JC}}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	∘C/W

**Package Outlines and Ordering Information** 

Device Marking	Device	Reel Size	Tape Width	Quantity	
FDS3580	FDS3580	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Char	acteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	80			V	
ΔBVDSS ΔTJ	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		81		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA	
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
On Char	acteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250  \mu A$	2	2.5	4	V	
$\frac{\Delta VGS(th)}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-7		mV/°C	
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 7.6 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 7.6 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 7 \text{ A}$		0.022 0.037 0.024	0.027 0.055 0.031	Ω	
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	30			Α	
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 7.6 \text{ A}$		28		S	
Dvnamio	Characteristics						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1800		pF	
Coss	Output Capacitance	f = 1.0 MHz		180		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			90		pF	
Switchin	ng Characteristics (Note 2)						
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 40 \text{ V}, I_D = 1 \text{ A},$		13	26	ns	
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		8	20	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	1		34	60	ns	
t <sub>f</sub>	Turn-Off Fall Time	1		16	30	ns	
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = 40 \text{ V}, I_{D} = 7.6 \text{ A},$		34	46	nC	
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		6.1		nC	
$Q_{gd}$	Gate-Drain Charge			6.9		nC	
Drain-Sc	ource Diode Characteristics and	d Maximum Ratings					
l <sub>s</sub>	Maximum Continuous Drain-Source Did				2.1	Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	<b>-</b>	0.74	1.2	V		

<sup>1:</sup> R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.







a) 50° C/W when mounted on a 1 in² pad of 2 oz. copper.

b) 105° C/W when mounted on a 0.04 in² pad of 2 oz. copper.

c) 125° C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2: Pulse Test: Pulse Width  $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$ 

# **Typical Characteristics**

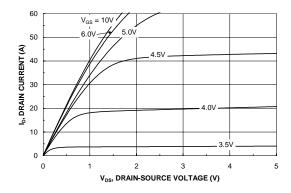


Figure 1. On-Region Characteristics.

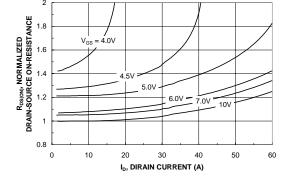


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

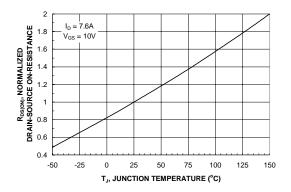


Figure 3. On-Resistance Variation with Temperature.

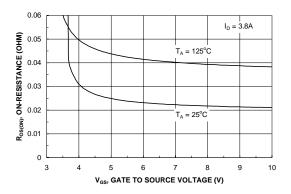


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

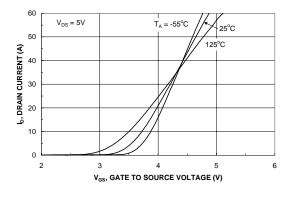


Figure 5. Transfer Characteristics.

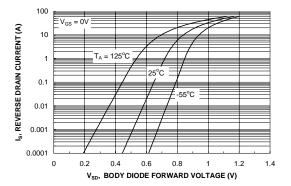
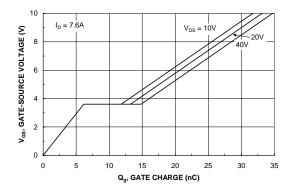


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# Typical Characteristics (continued)



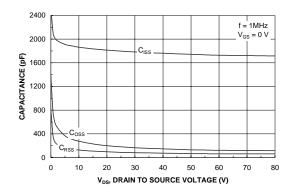
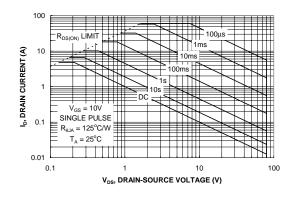


Figure 7. Gate-Charge Characteristics.





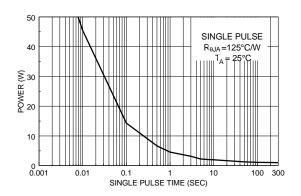


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

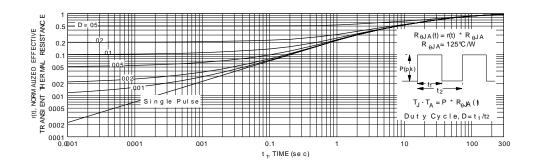
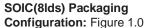


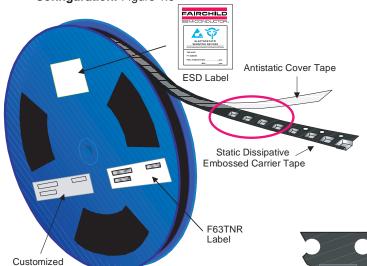
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

## SO-8 Tape and Reel Data and Package Dimensions





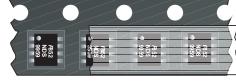


#### **Packaging Description:**

Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and amit-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 300cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (antistatic coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reles are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.





Packaging Option Standard o flow code) L86Z D84Z Rail/Tube TNR Packaging type TNR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 13" Dia 13" Dia 7" Dia 343y64y343 530x130x83 343y64y343 184v187v47 5,000 30,000 8,000 1,000

Box Dimension (mm) Max qty per Box Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC (8lds) Packaging Information

### **SOIC-8 Unit Orientation**

### F63TNR Label sample

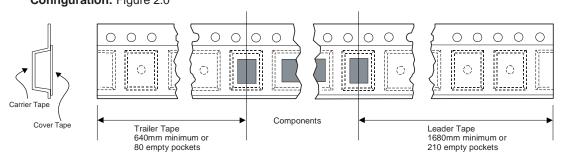
Label

Reel Size



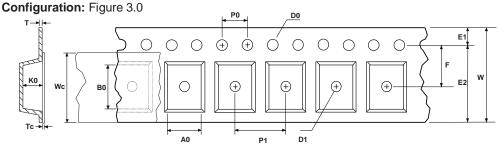
# 343mm x 342mm x 64mm Standard Intermediate box ESD Label F63TNL F63TN Label

### SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





# SOIC(8lds) Embossed Carrier Tape



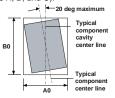


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

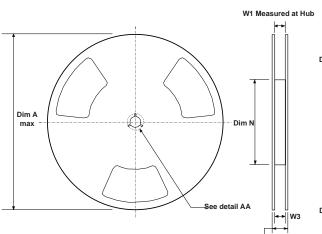
Component Rotation



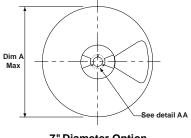
Sketch C (Top View)

Component lateral movement

### SOIC(8lds) Reel Configuration: Figure 4.0



13" Diameter Option



7" Diameter Option

B Min

Dim C

Dim D

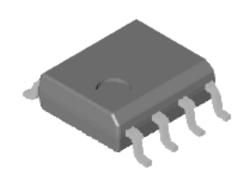
min

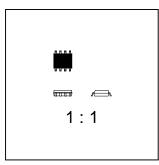
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

W2 max Measured at Hub

# SO-8 Tape and Reel Data and Package Dimensions, continued

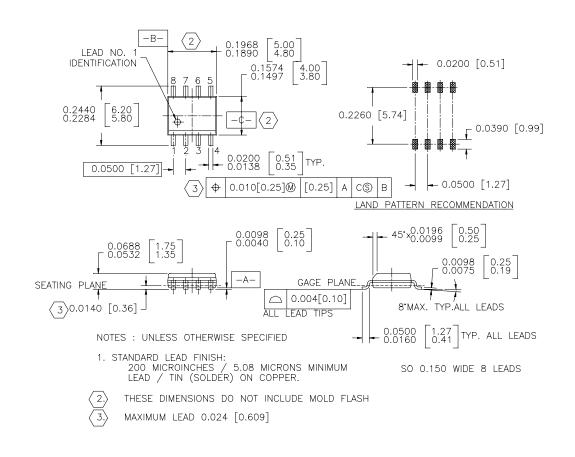
# SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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 $E^2CMOS^{TM}$  PowerTrench<sup>TM</sup>

FACT™ QFET™ FACT Quiet Series™ QS™

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Datasheet Identification	Product Status	Definition
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